Wuxi Unigroup Microelectronics CO.,LTD.

60V N-Channel Trench MOSFET

General Description

- Trench Power technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications

Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial

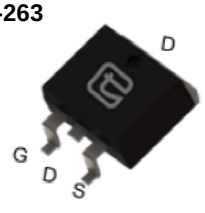
Product Summary

V_{DS}	60V
I_D (at V_{GS}=10V)	105A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 7.5mΩ

100% UIS Tested

RoHS

TO-263



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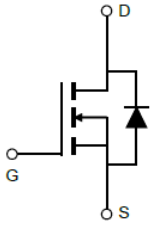


Part Number	Package Type	Form	Marking
TTB105N06A	TO-263	Tape&Reel	105N06A
TTP105N06A	TO-220	Tube	105N06A

Absolute Maximum Ratings (T_A =25ºC unless otherwise noted)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B]	T_C =25ºC	I_D	105	A
	T_C =100ºC		73.5	
Pulsed Drain Current [A]		I_{DM}	315	A
Avalanche Current [A]		I_{AS}	30	A
Single Pulse Avalanche Energy L =0.3mH [A]		E_{AS}	135	mJ
Power Dissipation [C]	T_C =25ºC	P_D	187.5	W
	T_C =100ºC		93.8	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	ºC

Thermal Characteristics

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	0.8	ºC/W
Maximum Junction-to-Ambient	Steady-State	$R_{\theta JA}$	100	

Electrical Characteristics(T_J =25ºC unless otherwise noted)							
Symbol	**Parameter**	**Conditions**		**Value**			**Units**
				Min	**Typ**	**Max**	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D =250μA,V_{GS} =0V		60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =60V, V_{GS} =0V	T_J =25ºC	--	--	1	μA
			T_J =100ºC	--	--	25	
I_{GSS}	Gate-Body Leakage Current	V_{DS} =0V, V_{GS} =±20V		--		±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} =V_{GS}, I_D =250μA		2	3	4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} =10V, I_D =30A		--	6.2	7.5	mΩ
g_{FS}	Forward Transconductance	V_{DS} =10V, I_D =25A		--	25	--	S
V_{SD}	Diode Forward Voltage	I_S =30A, V_{GS} =0V		--	--	1	V
I_S	Maximum Body-Diode Continuous Current [B]			--	--	105	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS} =0V, V_{DS} =30V, f =1MH_Z		--	4211	--	pF
C_{oss}	Output Capacitance			--	298	--	
C_{rss}	Reverse Transfer Capacitance			--	264	--	
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS} =10V,V_{DS} =30V, I_D =30A		--	82	--	nC
Q_{gs}	Gate Source Charge			--	22	--	
Q_{gd}	Gate Drain Charge			--	23	--	
$t_{D(on)}$	Turn-On Delay Time	V_{GS} =10V,V_{DS} =30V, I_D =30A, R_G =3Ω		--	20	--	ns
t_r	Turn-On Rise Time			--	18	--	
$T_{D(off)}$	Turn-Off Delay Time			--	50	--	
t_f	Turn-Off Fall Time			--	80	--	
t_{rr}	Body Diode Reverse Recovery Time	I_F =20A, di/dt =100A/μs		--	50	--	ns
Q_{rr}	Body Diode Reverse Recovery Charge			--	95	--	nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)}$ =175ºC, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

Typical Characteristics T_J = 25ºC, unless otherwise noted

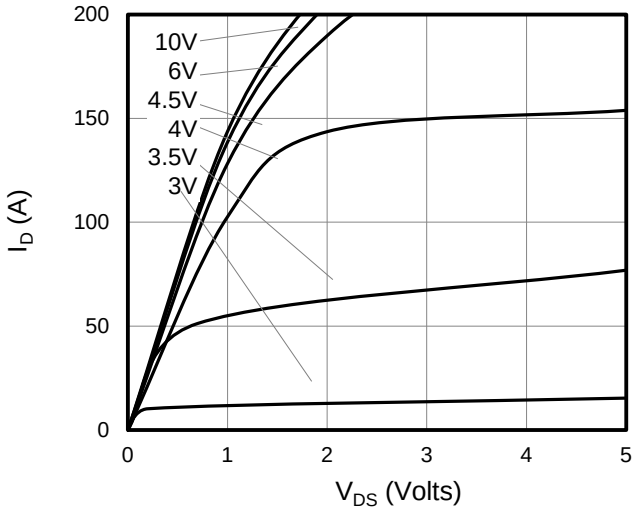


Figure 1: On-Region Characteristics

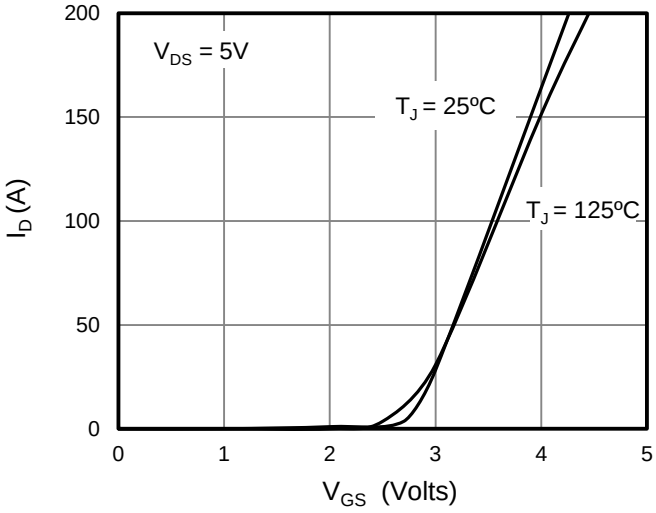


Figure 2: Transfer Characteristics

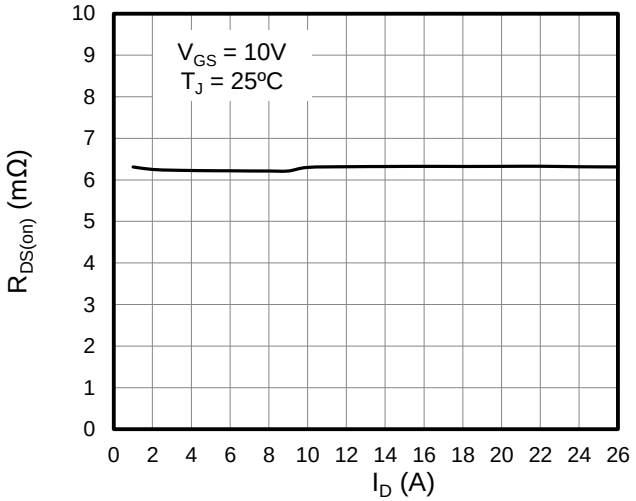


Figure 3: On-Resistance vs. Drain Current

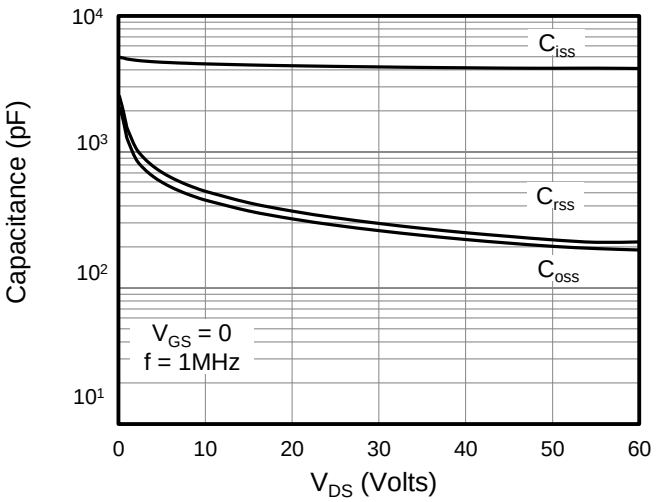


Figure 4: Capacitance Characteristics

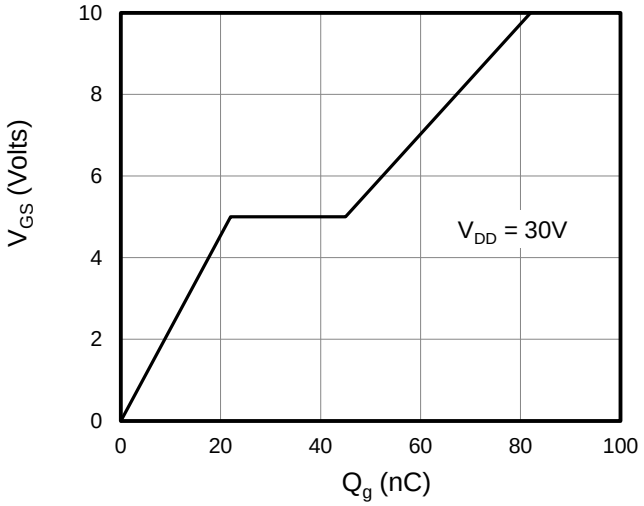


Figure 5: Gate Charge Characteristics

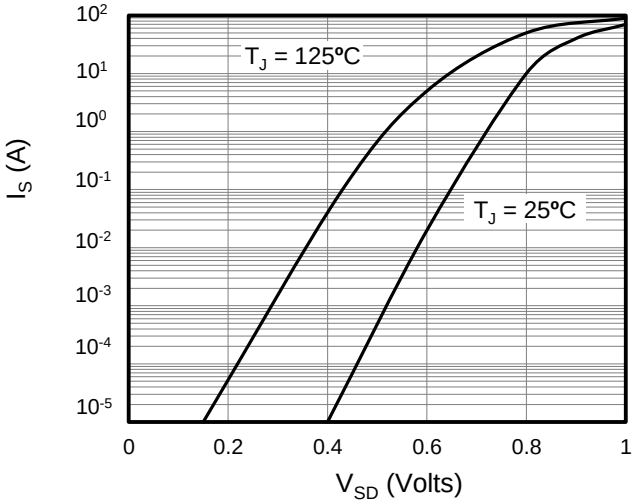


Figure 6: Body Diode Forward Voltage

Typical Characteristics T_J = 25ºC, unless otherwise noted

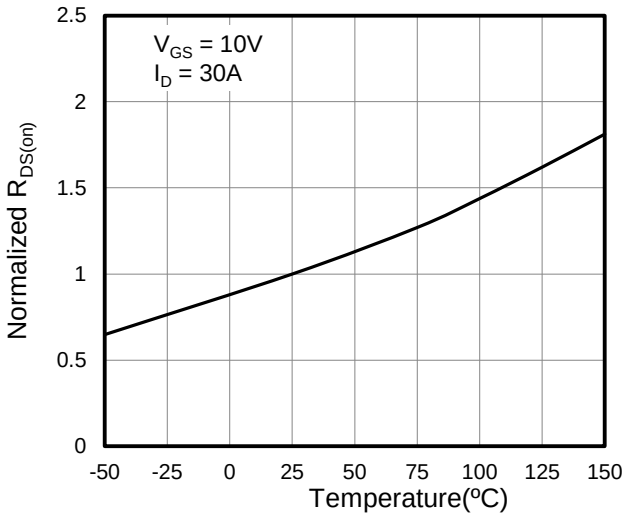


Figure 7: On-Resistance vs. Junction Temperature

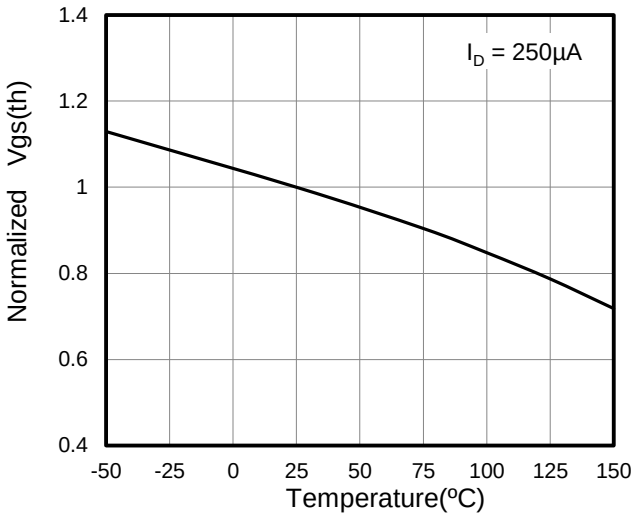


Figure 8: Vgs(th) vs. Junction Temperature

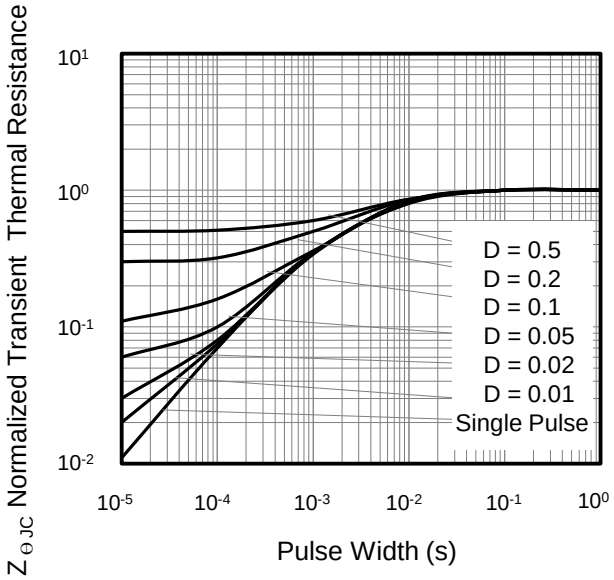


Figure 9: Normalized Transient Thermal Resistance

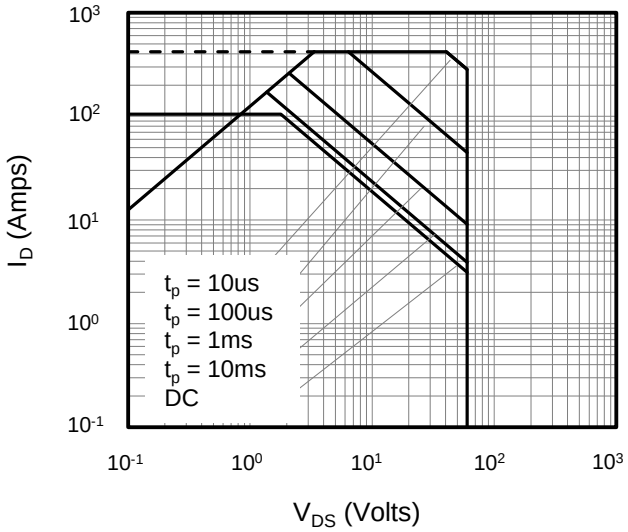


Figure 10: Safe Operating Area

Figure A：Gate Charge Test Circuit and Waveform

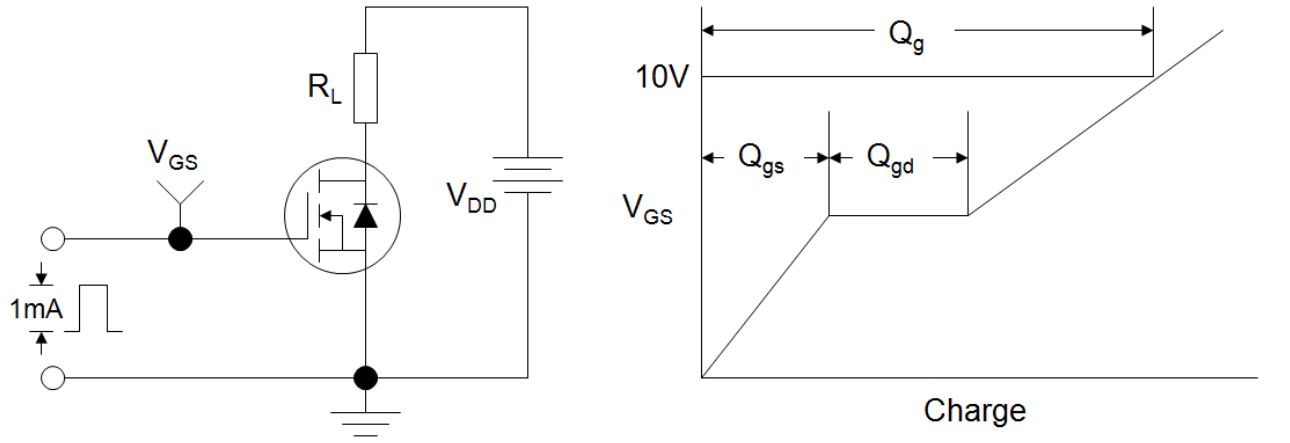


Figure B：Resistive Switching Test Circuit and Waveform

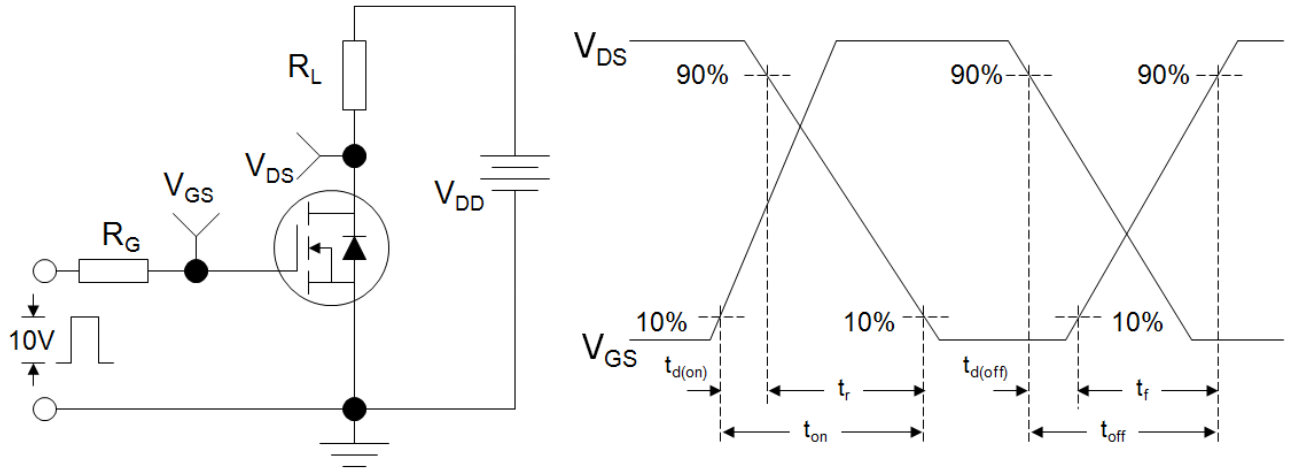
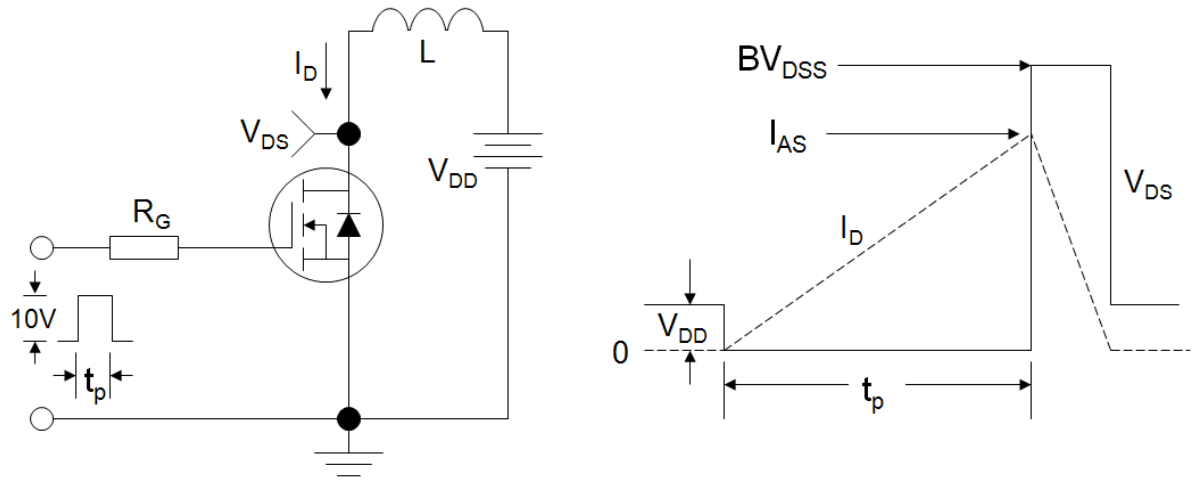
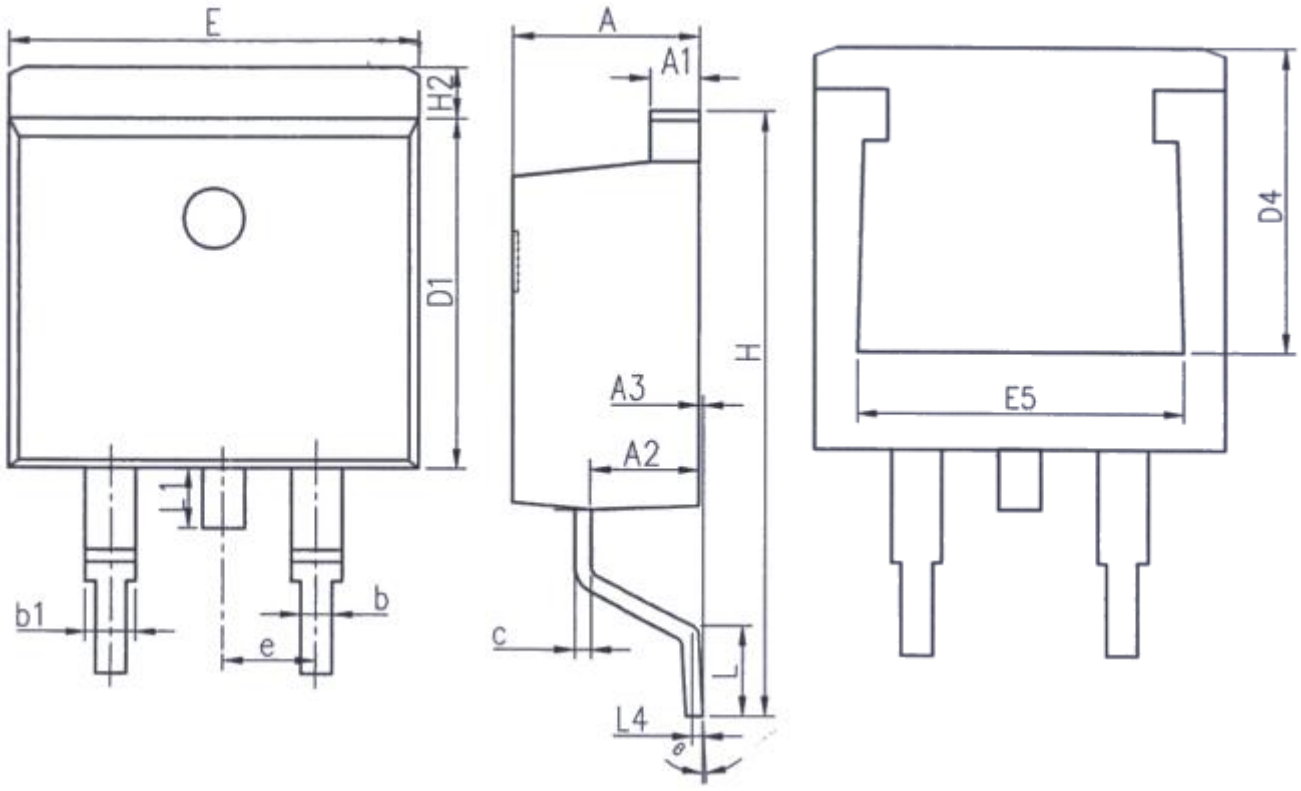


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



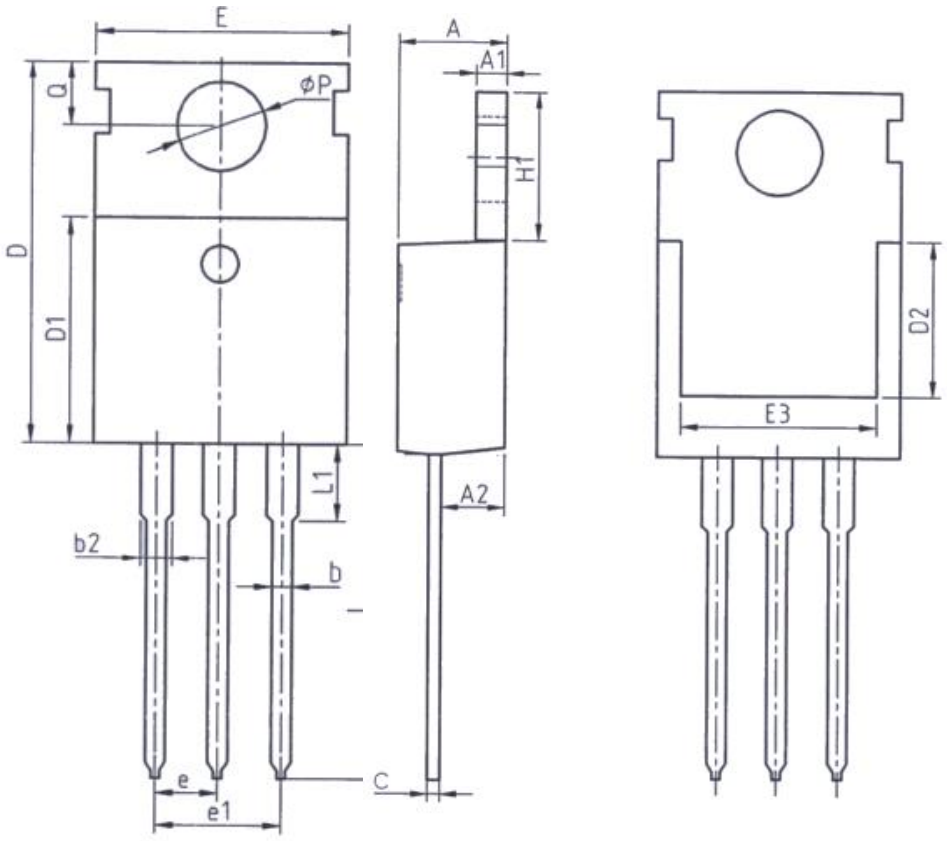
TO-263(华天)



Unit：mm			
Symbol	Min	Nom	Max
A	4.40	4.50	4.60
A1	1.25	1.30	1.35
A2	2.20	2.40	2.60
A3	0	0.10	0.25
b	0.76	-	0.89
b1	1.23	-	1.37
c	0.47	-	0.60
D1	9.10	9.20	9.30
D4	8.00	-	-

Unit：mm			
Symbol	Min	Nom	Max
E	9.80	9.90	10.00
E5	7.80	-	-
e	2.54BSC		
H	14.90	15.30	15.70
H2	1.17	1.27	1.40
L	2.00	2.30	2.60
L1	-	-	1.75
L4	0.25BSC		
θ	0^o		8^o

TO-220(华天)



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	–

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	–
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	–	3.40
P	3.40	3.80
Q	2.60	3.00

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